

LOW VCE(SAT) NPN SURFACE MOUNT TRANSISTOR

Features

- BV_{CEO} > 50V
- I_C = 3.0A Continuous Current
- Complementary PNP Type Available (DPLS350Y)
- Ideally Suited for Automated Assembly Processes
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability

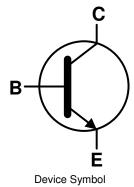
Mechanical Data

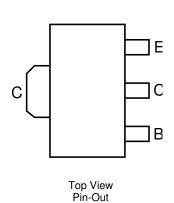
- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.052 grams (Approximate)

Applications

• Ideal for Medium Power Switching or Amplification Applications







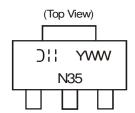
Ordering Information (Note 4)

Device	Package	Shipping
DNLS350Y-13	SOT89	2500/Tape & Reel

Notes::

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ ☐ Manufacturer's Marking

N35 = Product Type Marking Code

YWW = Date Code Marking

Y = Last Digit of Year (ex: 7 = 2017)

WW = Week Code (01 to 52)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	5	Α
Continuous Collector Current	Ic	3	Α
Base Current	I _B	0.5	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		1	W	
Power Dissipation	(Note 6)	P_{D}	1.6		
	(Note 7)		2.0		
	(Note 5)		125		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	78	°C/W	
	(Note 7)		62.5		
Thermal Resistance, Junction to Lead	(Note 8)	$R_{ heta JL}$	5.7	°C/W	
Operating and Storage Temperature Range	•	T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

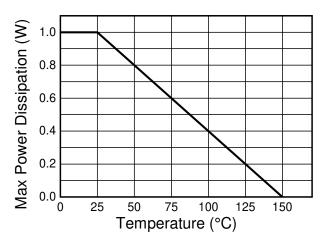
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

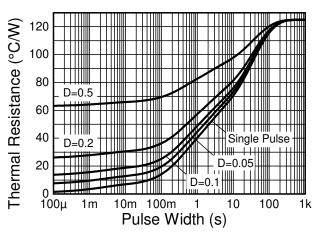
Notes:

- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



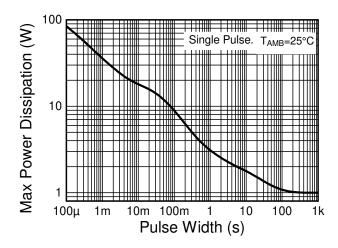
Thermal Characteristics and Derating Information

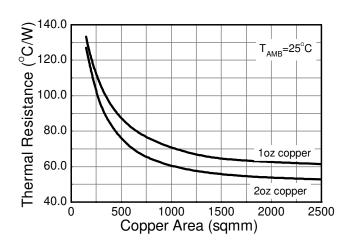


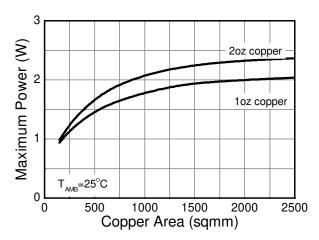


Derating Curve

Transient Thermal Impedance









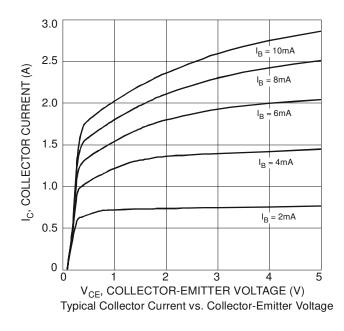
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

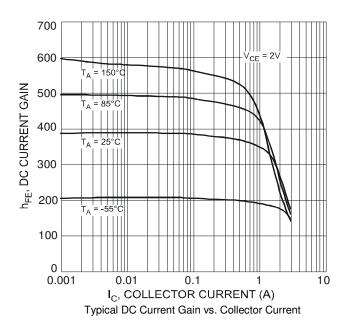
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	$V_{CB} = 50V, I_{E} = 0$	
		_	_	50	μΑ	$V_{CB} = 50V, I_E = 0, T_A = +150$ °C	
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$	
Collector-Emitter Cutoff Current	I _{CES}	_	_	100	nA	$V_{CE} = 50V, V_{BE} = 0$	
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage	BV_CEO	50		_	V	$I_C = 10mA$	
Emitter-Base Breakdown Voltage	BV _{EBO}	5		_	V	$I_E = 100 \mu A$	
ON CHARACTERISTICS (Note 10)							
		300	_	_		$V_{CE} = 2V, I_{C} = 0.1A$	
		300	_	_		$V_{CE} = 2V, I_{C} = 0.5A$	
DC Current Gain	h _{FE}	300		700		$V_{CE} = 2V$, $I_C = 1A$	
		200		_		$V_{CE} = 2V$, $I_C = 2A$	
		100		_		$V_{CE} = 2V$, $I_C = 3A$	
		_	38	80		$I_C = 0.5A, I_B = 50mA$	
		_	70	160		$I_C = 1A$, $I_B = 50mA$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	130	280	mV	$I_C = 2A$, $I_B = 100mA$	
				_	124	260	
		_	180	370		$I_C = 3A$, $I_B = 300mA$	
Equivalent On-Resistance	R _{CE(SAT)}	_	62	130	$m\Omega$	$I_E = 2A$, $I_B = 200mA$	
Base-Emitter Saturation Voltage		_		1.1	V	I _C = 2A, I _B = 100mA	
base-Emilier Saturation voltage	$V_{BE(SAT)}$	_	_	1.2	V	$I_C = 3A$, $I_B = 300mA$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_		1.1	V	$V_{CE} = 2V$, $I_C = 1A$	
SMALL SIGNAL CHARACTERISTICS							
Transition Frequency	f _T	100		_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz	
Output Capacitance	C _{obo}	_		25	pF	V _{CB} = 10V, f = 1MHz	

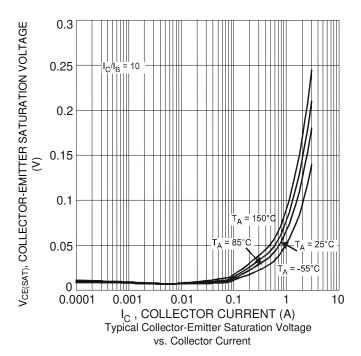
Notes: 10. Measured under pulsed conditions. Pulse width = $300 \, \mu s$. Duty cycle $\leq 2\%$.

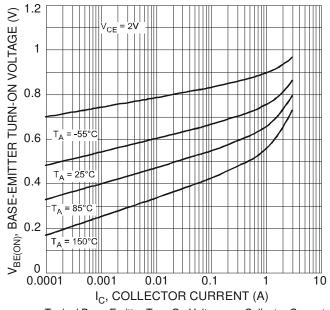


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



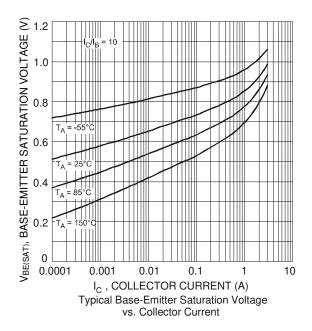


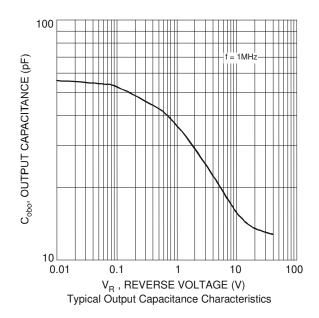


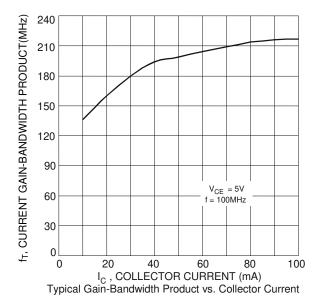




Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.) (Cont.)





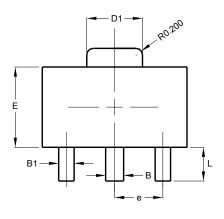


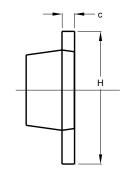


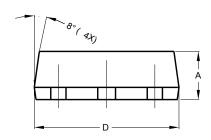
Package Outline Dimensions

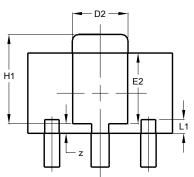
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







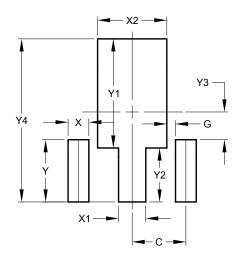


SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
E	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

Suggested Pad Layout

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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